



ELECTRONICS INDUSTRY (USA) CO., LTD.

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捷多邦, 专业PCB打样工厂, 24小时加急出货



Certificate Number: Q10561



Certificate Number: E17276

BR5000 - BR5010

PRV : 50 - 1000 Volts

Io : 50 Amperes

FEATURES :

- * High case dielectric strength
- * High surge current capability
- * High reliability
- * High efficiency
- * Low reverse current
- * Low forward voltage drop

MECHANICAL DATA :

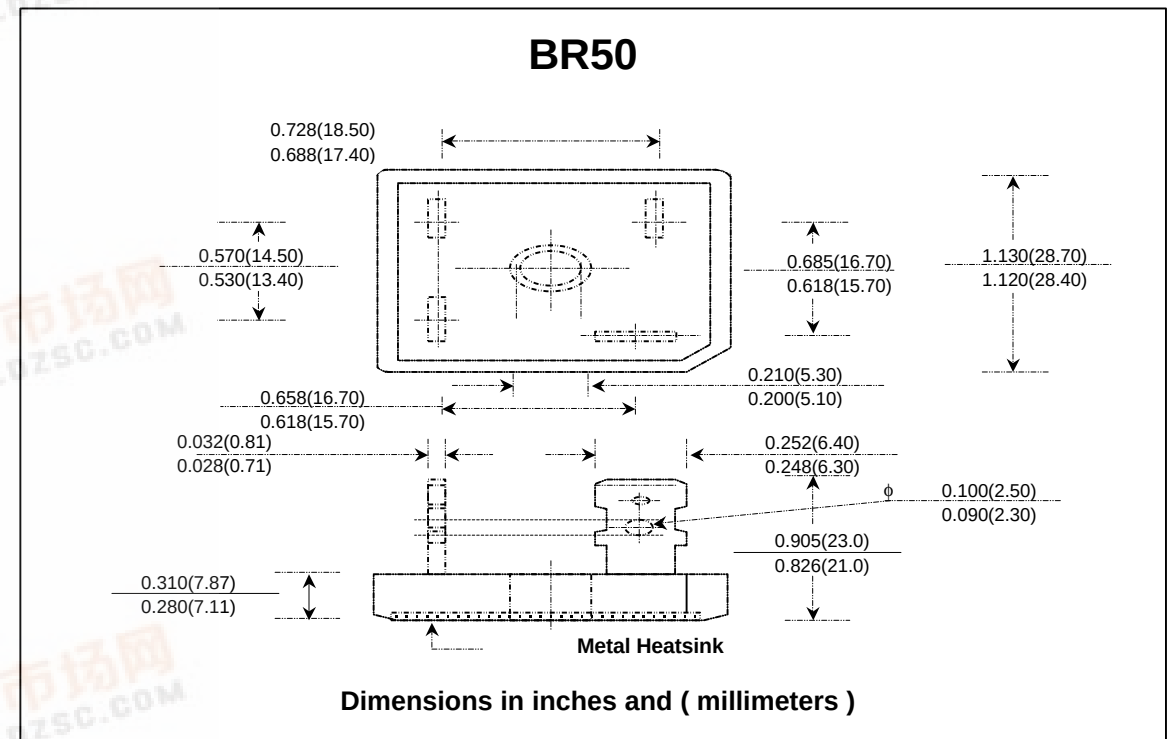
- * Case : Molded plastic with heatsink integrally mounted in the bridge encapsulation
- * Epoxy : UL94V-O rate flame retardant
- * Terminals : plated .25" (6.35 mm). Faston
- * Polarity : Polarity symbols marked on case
- * Mounting position : Bolt down on heat-sink with silicone thermal compound between bridge and mounting surface for maximum heat transfer efficiency.
- * Weight : 17.1 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

RATING	SYMBOL	BR5000	BR5001	BR5002	BR5004	BR5006	BR5008	BR5010	UNIT
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Current T _c = 55°C	I _{F(AV)}	50							Amps.
Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	I _{FSM}	500							Amps.
Current Squared Time at t < 8.3 ms.	I ² t	660							A ² S
Maximum Forward Voltage per Diode at I _F =25 Amp.	V _F	1.1							Volts
Maximum DC Reverse Current Ta = 25 °C	I _R	10							μA
at Rated DC Blocking Voltage Ta = 100 °C	I _{R(H)}	200							μA
Typical Thermal Resistance (Note 1)	R _{θJC}	1.0							°C/W
Operating Junction Temperature Range	T _J	- 40 to + 150							°C
Storage Temperature Range	T _{STG}	- 40 to + 150							°C

SILICON BRIDGE RECTIFIERS





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RATING AND CHARACTERISTIC CURVES (BR5000 - BR5010)

FIG.1 - DERATING CURVE FOR OUTPUT
RECTIFIED CURRENT

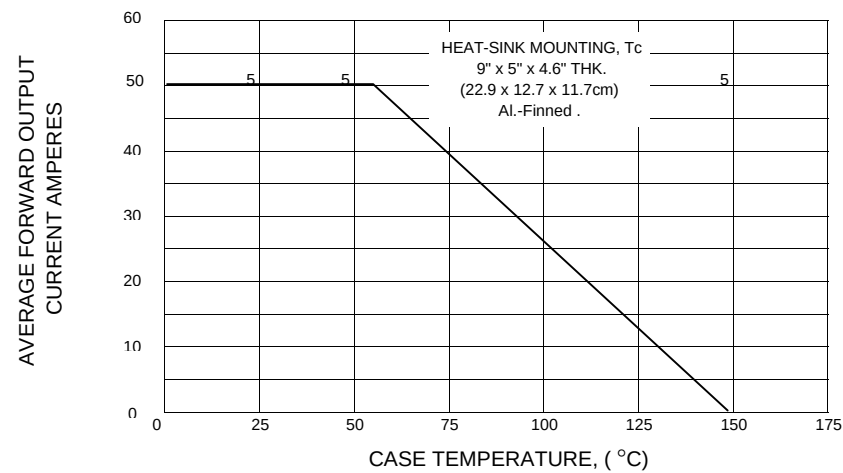


FIG.2 - MAXIMUM NON-REPETITIVE PEAK
FORWARD SURGE CURRENT

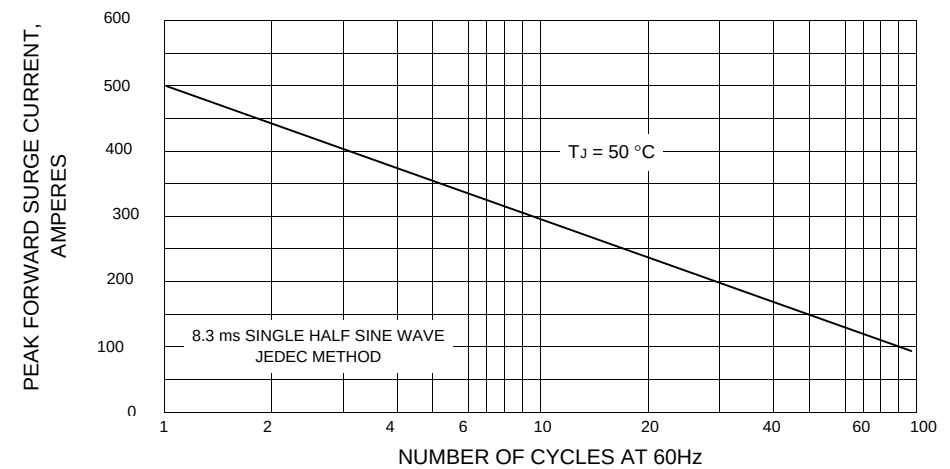


FIG.3 - TYPICAL FORWARD CHARACTERISTICS
PER DIODE

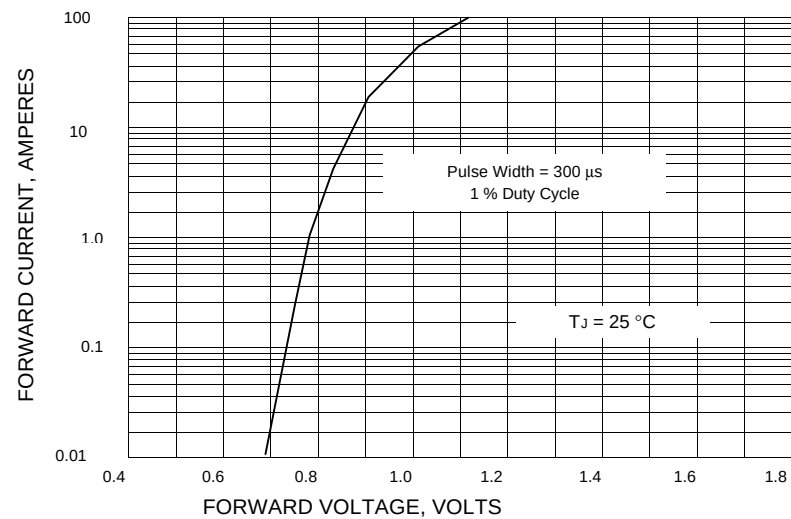


FIG.4 - TYPICAL REVERSE CHARACTERISTICS
PER DIODE

